

PBSS306NX

100 V, 4.5 A NPN low V_{CEsat} (BISS) transistor

Rev. 01 — 21 August 2006

Product data sheet

1. Product profile

1.1 General description

NPN low V_{CEsat} Breakthrough In Small Signal (BISS) transistor in a SOT89 (SC-62/TO-243) small and flat lead Surface-Mounted Device (SMD) plastic package.

PNP complement: PBSS306PX.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- High-voltage DC-to-DC conversion
- High-voltage MOSFET gate driving
- High-voltage motor control
- High-voltage power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. Quick reference data

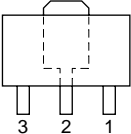
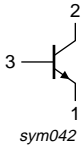
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	100	V
I_C	collector current		-	-	4.5	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	9	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 4$ A; $I_B = 200$ mA	[1] -	40	56	m Ω

[1] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

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2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	emitter		
2	collector		
3	base		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PBSS306NX	SC-62	plastic surface-mounted package; collector pad for good heat transfer; 3 leads	SOT89

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PBSS306NX	*5G

- [1] * = -: made in Hong Kong
 * = p: made in Hong Kong
 * = t: made in Malaysia
 * = W: made in China

5. Limiting values

Table 5. Limiting values

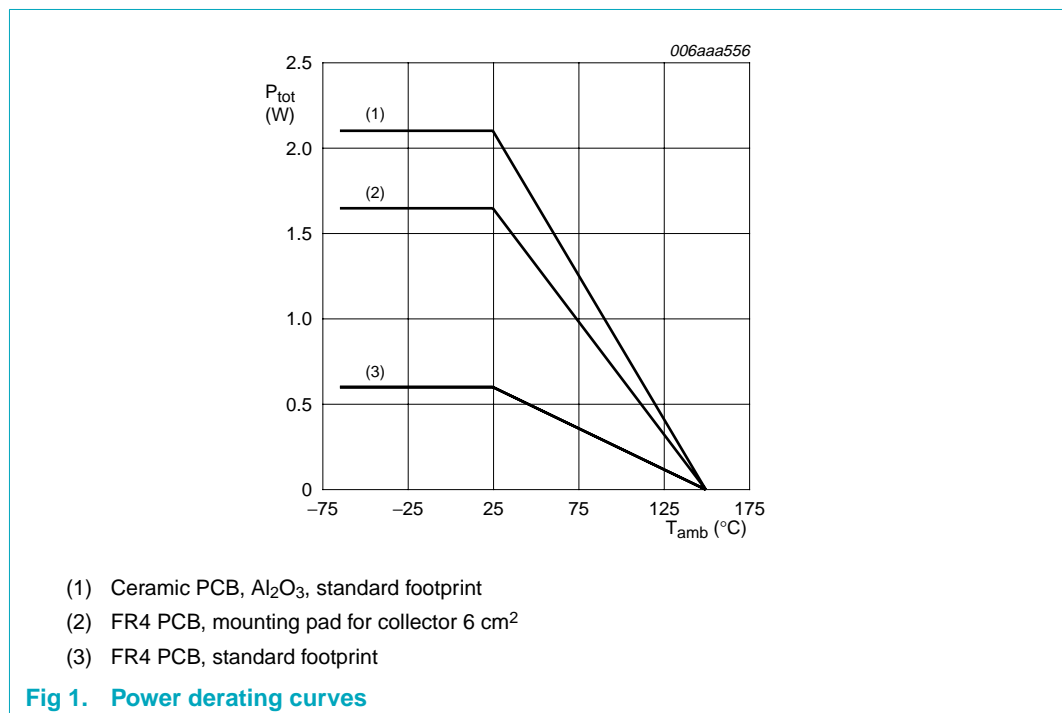
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
V_{CBO}	collector-base voltage	open emitter	-	100	V	
V_{CEO}	collector-emitter voltage	open base	-	100	V	
V_{EBO}	emitter-base voltage	open collector	-	5	V	
I_C	collector current		-	4.5	A	
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	9	A	
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C	[1]	-	0.6	W
			[2]	-	1.65	W
			[3]	-	2.1	W
T_j	junction temperature		-	150	°C	
T_{amb}	ambient temperature		-65	+150	°C	
T_{stg}	storage temperature		-65	+150	°C	

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

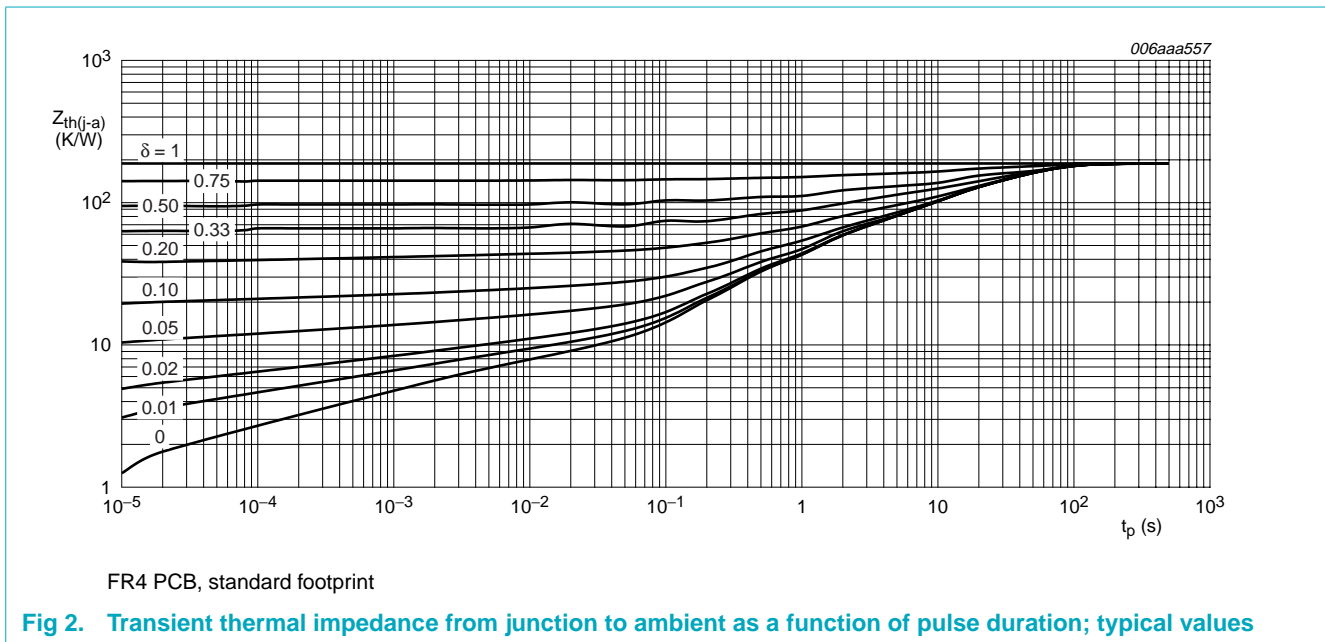


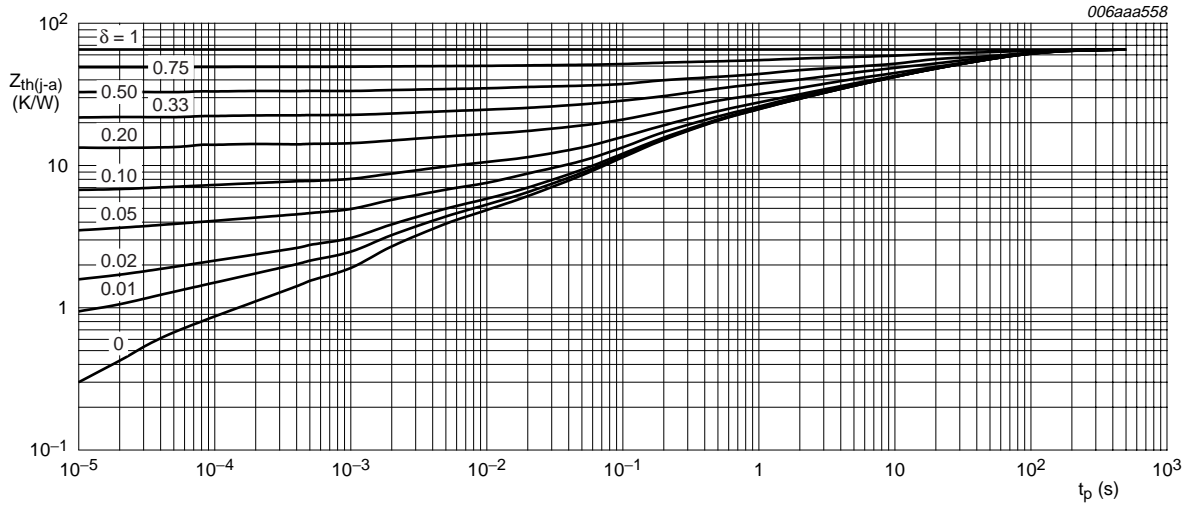
6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	208	K/W
			[2]	-	-	76	K/W
			[3]	-	-	60	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	20	K/W	

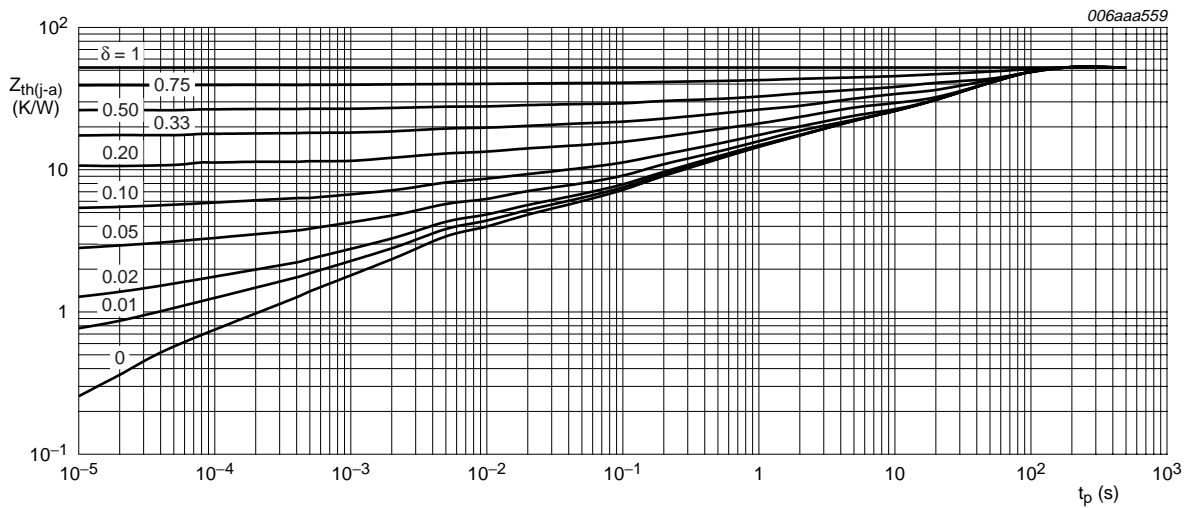
- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.





FR4 PCB, mounting pad for collector 6 cm²

Fig 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



Ceramic PCB, Al₂O₃, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

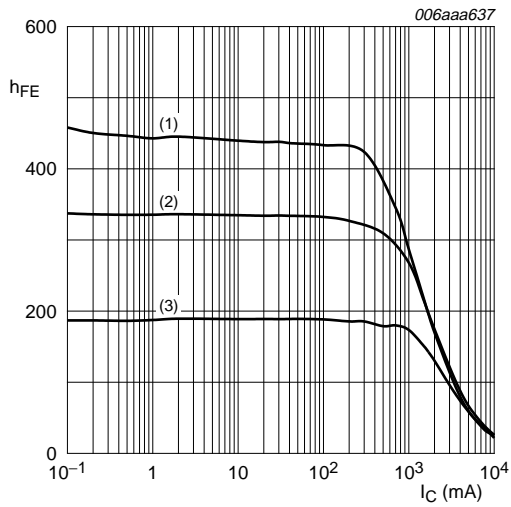
7. Characteristics

Table 7. Characteristics

$T_{amb} = 25^\circ\text{C}$ unless otherwise specified.

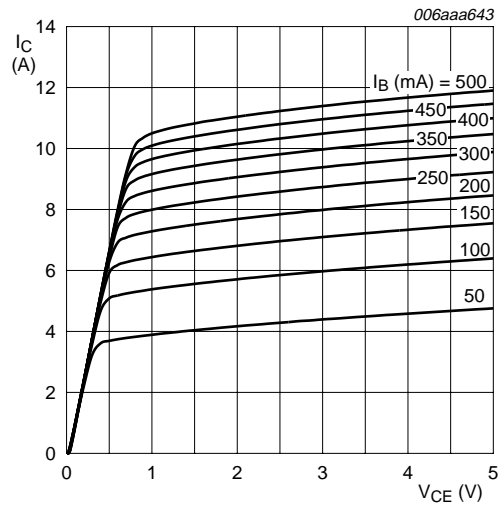
Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
I_{CBO}	collector-base cut-off current	$V_{CB} = 80\text{ V}; I_E = 0\text{ A}$	-	-	100	nA	
		$V_{CB} = 80\text{ V}; I_E = 0\text{ A}; T_j = 150^\circ\text{C}$	-	-	50	μA	
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA	
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}; I_C = 0.5\text{ A}$	[1]	200	330	-	
		$V_{CE} = 2\text{ V}; I_C = 1\text{ A}$	[1]	150	270	-	
		$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	[1]	100	175	-	
		$V_{CE} = 2\text{ V}; I_C = 4\text{ A}$	[1]	50	85	-	
		$V_{CE} = 2\text{ V}; I_C = 5\text{ A}$	[1]	40	70	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 0.5\text{ A}; I_B = 50\text{ mA}$	[1]	-	27	40	mV
		$I_C = 1\text{ A}; I_B = 50\text{ mA}$	[1]	-	53	75	mV
		$I_C = 1\text{ A}; I_B = 10\text{ mA}$	[1]	-	100	150	mV
		$I_C = 2\text{ A}; I_B = 40\text{ mA}$	[1]	-	115	160	mV
		$I_C = 4\text{ A}; I_B = 200\text{ mA}$	[1]	-	160	225	mV
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1]	-	140	200	mV
		$I_C = 4.5\text{ A}; I_B = 225\text{ mA}$	[1]	-	170	245	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 4\text{ A}; I_B = 200\text{ mA}$	[1]	-	40	56	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1]	-	0.81	0.9	V
		$I_C = 4\text{ A}; I_B = 400\text{ mA}$	[1]	-	0.94	1.05	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 2\text{ A}$	[1]	-	0.78	0.85	V
t_d	delay time	$V_{CC} = 12.5\text{ V}; I_C = 3\text{ A}; I_{Bon} = 0.15\text{ A}; I_{Boff} = -0.15\text{ A}$	-	15	-	ns	
t_r	rise time		-	315	-	ns	
t_{on}	turn-on time		-	330	-	ns	
t_s	storage time		-	240	-	ns	
t_f	fall time		-	290	-	ns	
t_{off}	turn-off time		-	530	-	ns	
f_T	transition frequency		$V_{CE} = 10\text{ V}; I_C = 100\text{ mA}; f = 100\text{ MHz}$	-	110	-	MHz
C_C	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	23	40	pF	

[1] Pulse test: $t_p \leq 300\ \mu\text{s}; \delta \leq 0.02$.



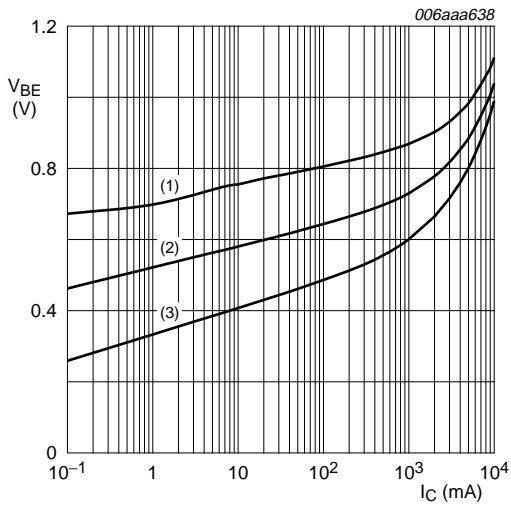
$V_{CE} = 2\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 5. DC current gain as a function of collector current; typical values



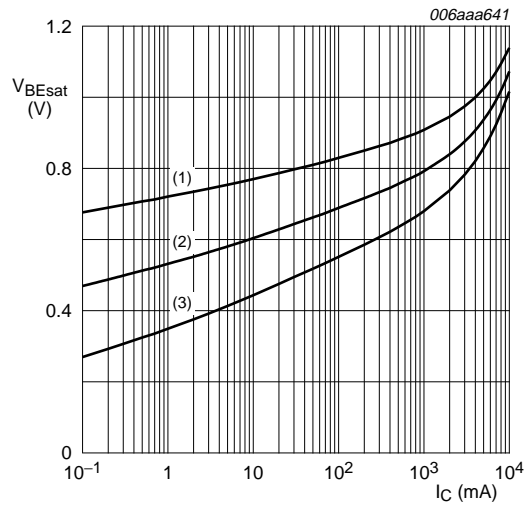
$T_{amb} = 25\text{ °C}$

Fig 6. Collector current as a function of collector-emitter voltage; typical values



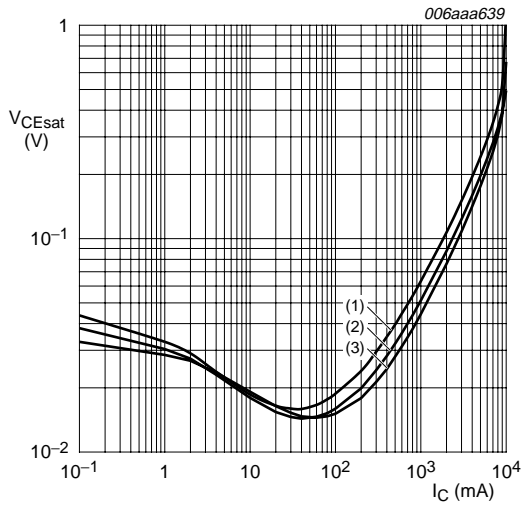
$V_{CE} = 2\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 7. Base-emitter voltage as a function of collector current; typical values



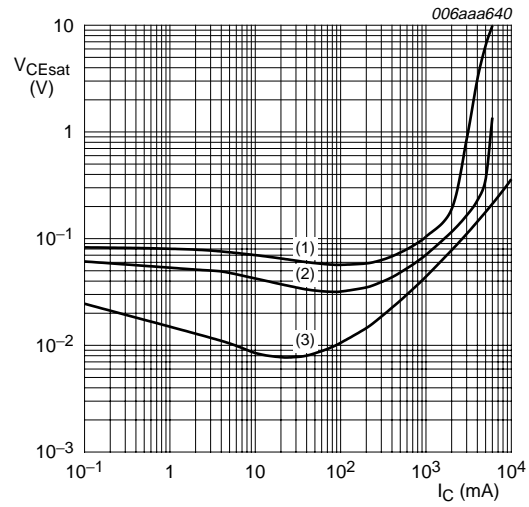
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 8. Base-emitter saturation voltage as a function of collector current; typical values



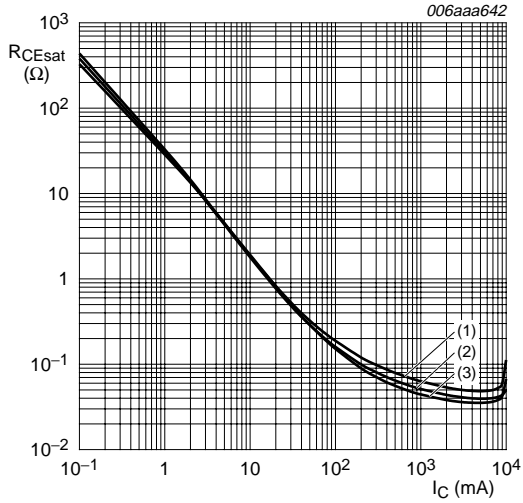
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 9. Collector-emitter saturation voltage as a function of collector current; typical values



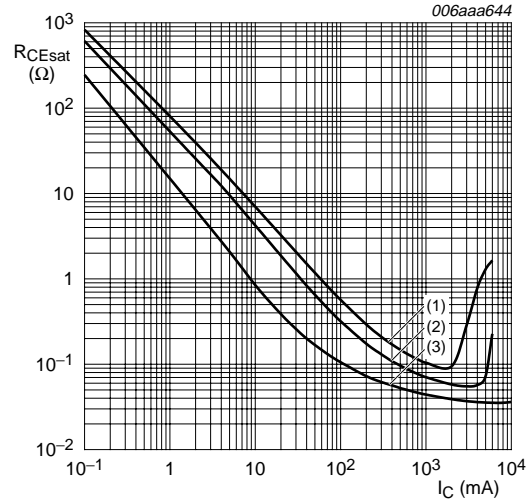
$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 10. Collector-emitter saturation voltage as a function of collector current; typical values



$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 11. Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 12. Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

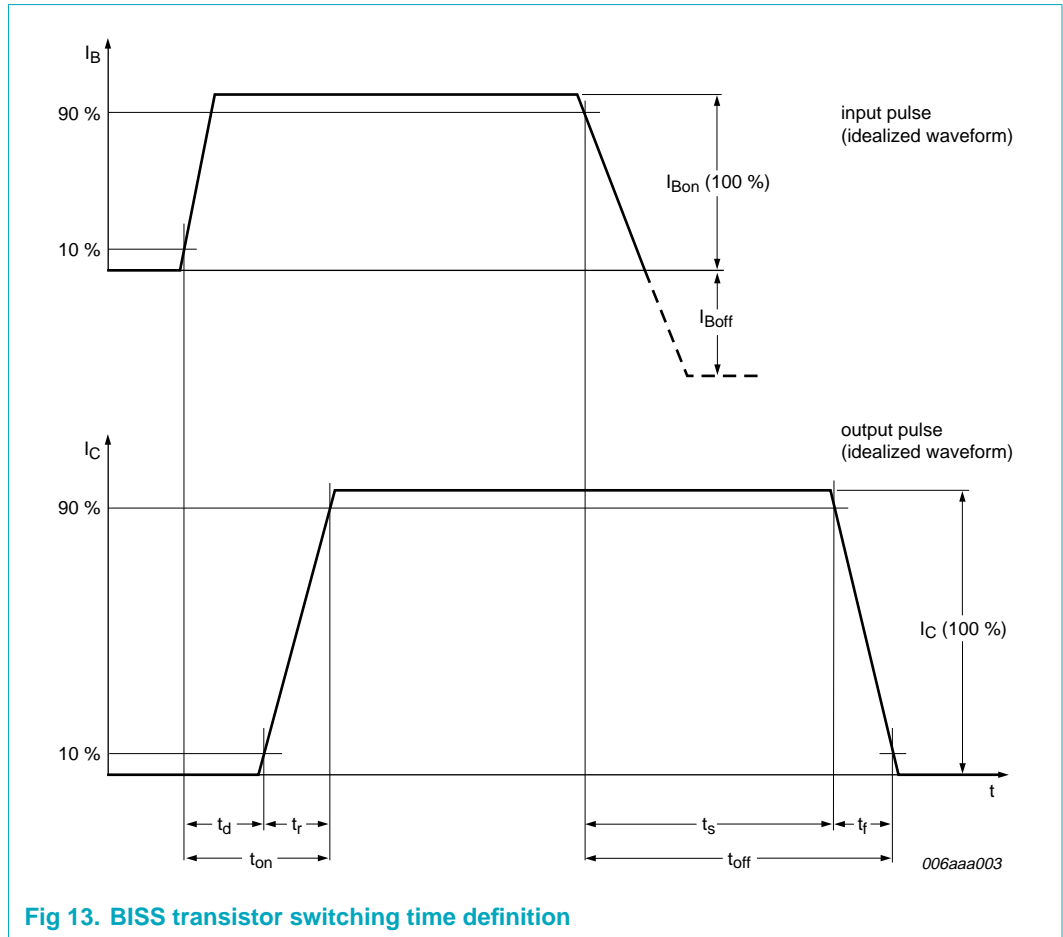
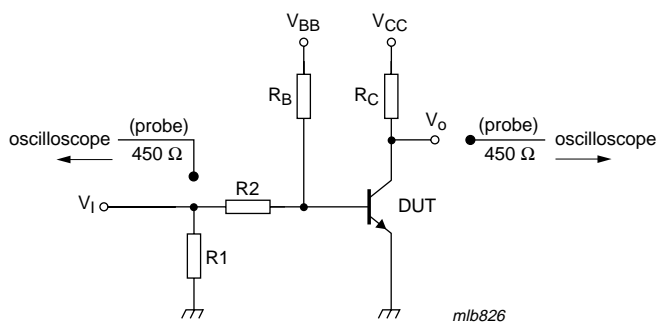


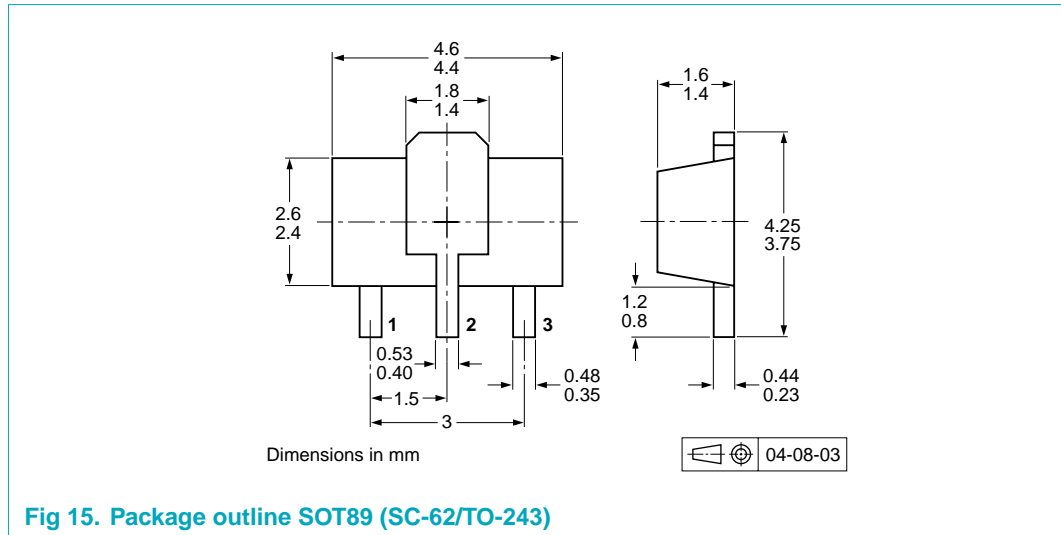
Fig 13. BISS transistor switching time definition



$V_{CC} = 12.5 \text{ V}; I_C = 3 \text{ A}; I_{Bon} = 0.15 \text{ A}; I_{Boff} = -0.15 \text{ A}$

Fig 14. Test circuit for switching times

9. Package outline



10. Packing information

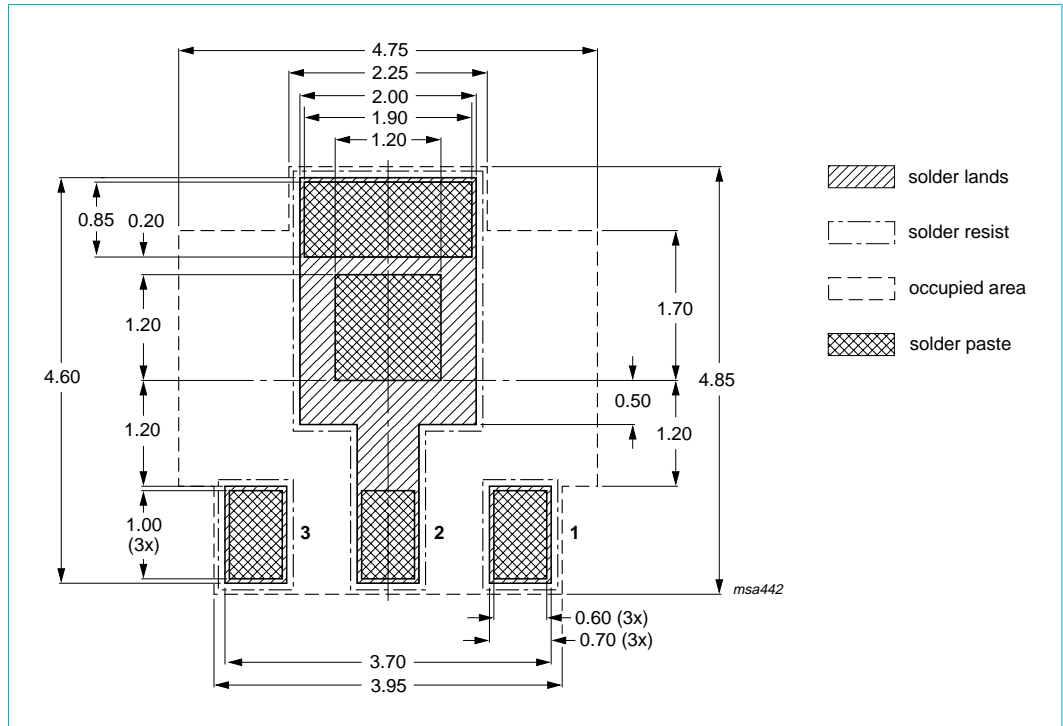
Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number	Package	Description	Packing quantity	
			1000	4000
PBSS306NX	SOT89	8 mm pitch, 12 mm tape and reel	-115	-135

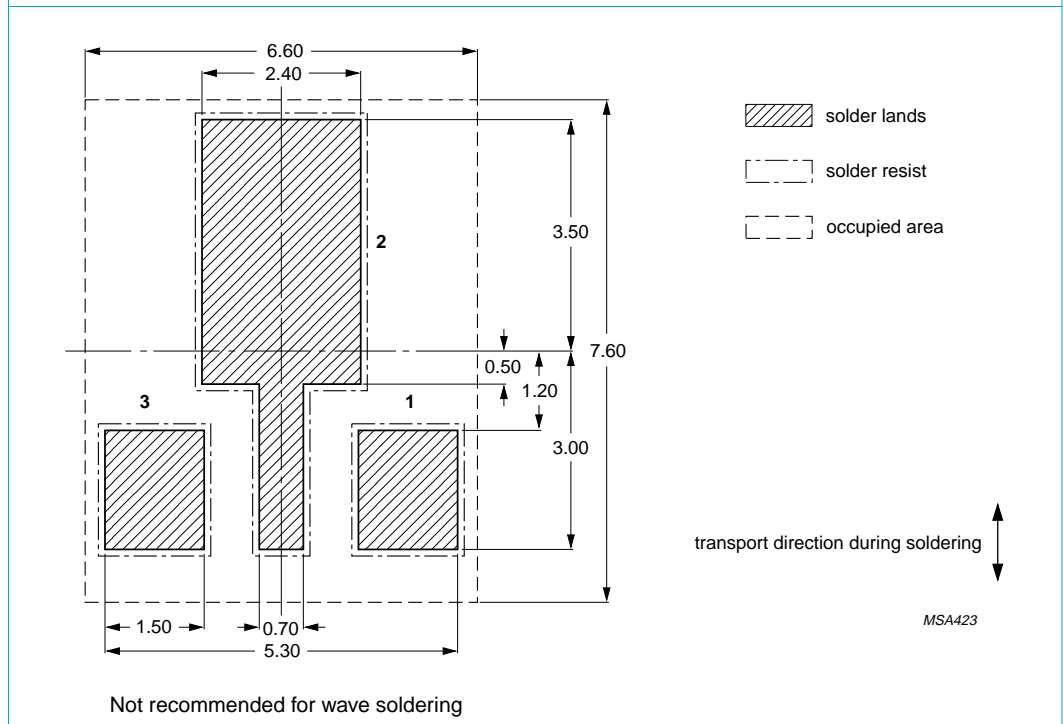
[1] For further information and the availability of packing methods, see [Section 15](#).

11. Soldering



SOT89 standard mounting conditions for reflow soldering
Dimensions in mm

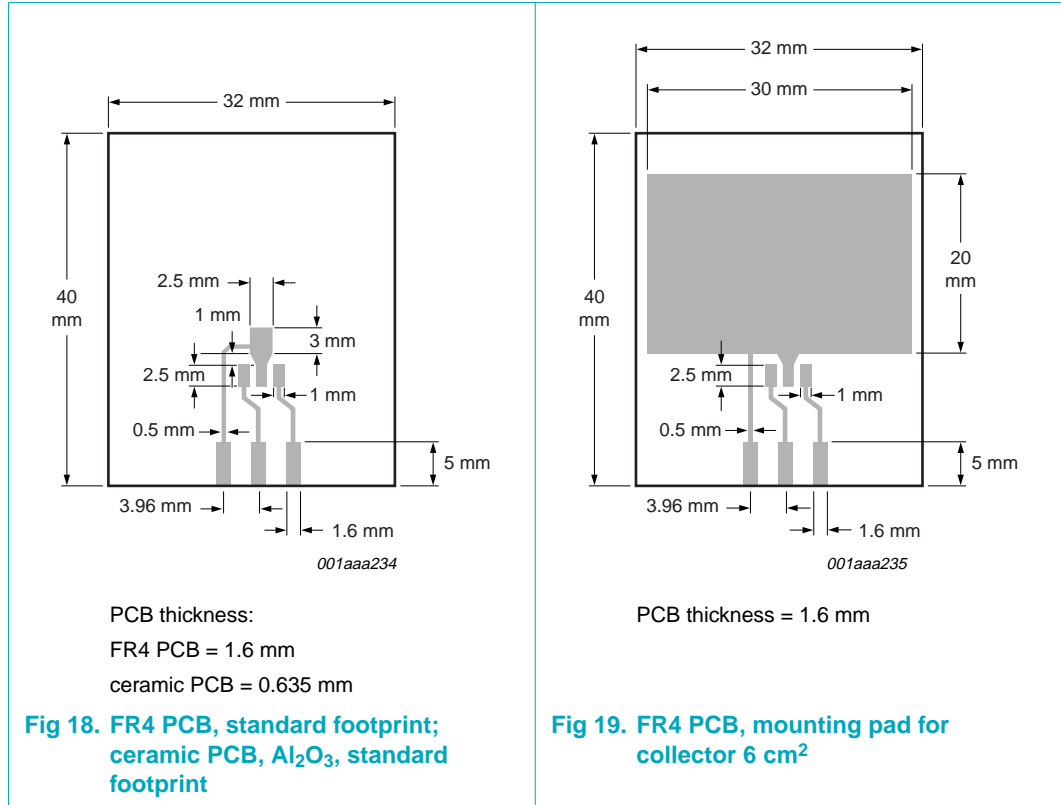
Fig 16. Reflow soldering footprint



Not recommended for wave soldering
Dimensions in mm

Fig 17. Wave soldering footprint

12. Mounting



13. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS306NX_1	20060821	Product data sheet	-	-

14. Legal information

14.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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